

	No.4661	2SA1881/2SC4983 PNP/NPN Epitaxial Planar Silicon Transistors Low-Frequency General-Purpose Amp Applications

Applications

- AF power amp, medium-speed switching, small-sized motor drivers and LED drivers.

Features

- Large current capacity.
- Low collector to emitter saturation voltage.
- Very small-sized package permitting 2SA1881/2SC4983-applied sets to be made smaller and slimmer.

() : 2SA1881

Absolute Maximum Ratings at Ta = 25°C

			unit
Collector-to-Base Voltage	V_{CBO}	(-)15	V
Collector-to-Emitter Voltage	V_{CEO}	(-)15	V
Emitter-to-Base Voltage	V_{EBO}	(-)5	V
Collector Current	I_C	(-)1	A
Collector Current(Pulse)	I_{CP}	(-)3	A
Base Current	I_B	(-)200	mA
Collector Dissipation	P_C	250	mW
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-55 to +150	°C

Electrical Characteristics at Ta = 25°C

			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = (-)12V, I_E = 0$			(-)100	nA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = (-)4V, I_C = 0$			(-)100	nA
DC Current Gain	$h_{FE}(1)$	$V_{CE} = (-)2V, I_C = (-)50mA$	135※		600※	
	$h_{FE}(2)$	$V_{CE} = (-)2V, I_C = (-)800mA$	80			
Gain-Bandwidth Product	f_T	$V_{CE} = (-)2V, I_C = (-)50mA$		(300)200		MHz
C-E Saturation Voltage	$V_{CE(sat)}(1)$	$I_C = (-)5mA, I_B = (-)0.5mA$		(-)10	(-)25	mV
	$V_{CE(sat)}(2)$	$I_C = (-)500mA, I_B = (-)25mA$		(-)120	(-)240	mV
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C = (-)500mA, I_B = (-)25mA$		(-)0.9	(-)1.2	V
Output Capacitance	C_{ob}	$V_{CB} = (-)10V, f = 1MHz$		(15)10		pF
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C = (-)10\mu A, I_E = 0$	(-)15			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C = (-)1mA, R_{BE} = \infty$	(-)15			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E = (-)10\mu A, I_C = 0$	(-)5			V

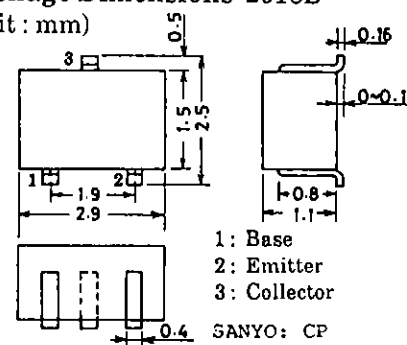
※ : The 2SA1881/2SC4983 are classified by 50mA h_{FE} as follows:

135	5	270	200	6	400	300	7	600
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Marking : 2SA1881 : IS
2SC4983 : KN

Package Dimensions 2018B

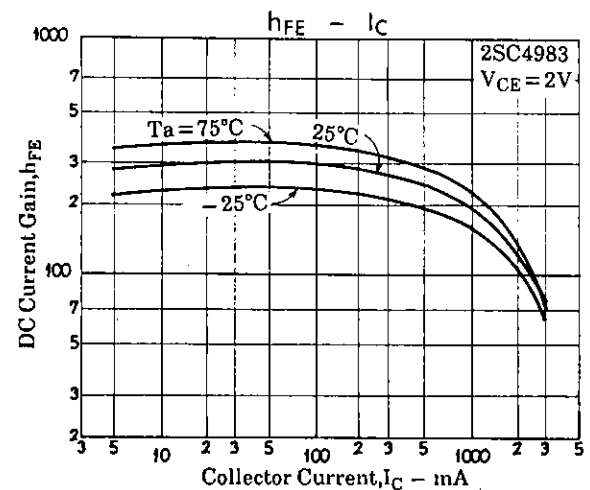
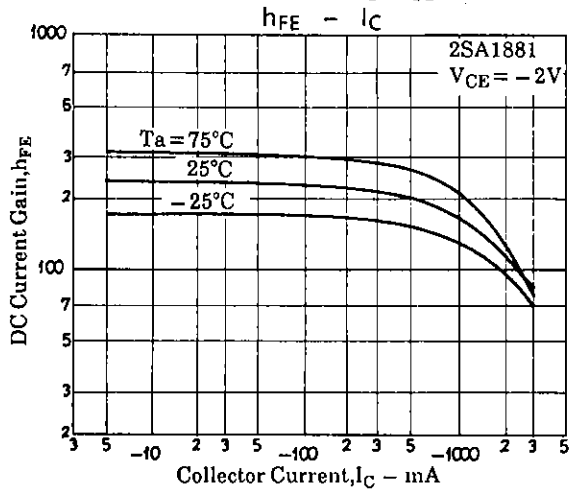
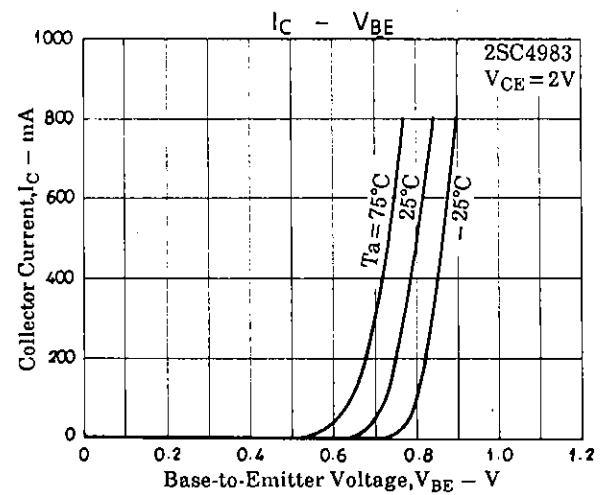
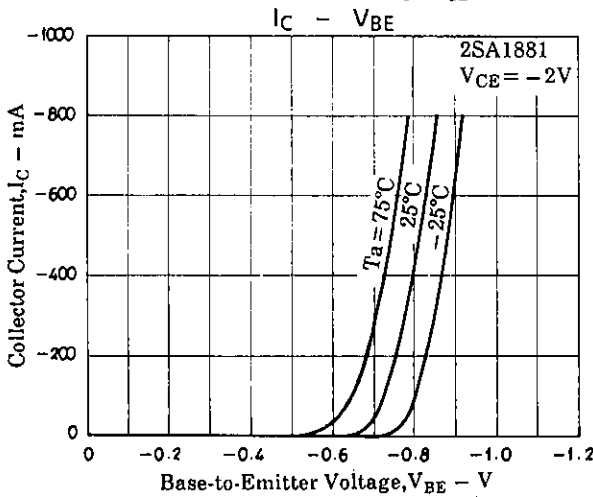
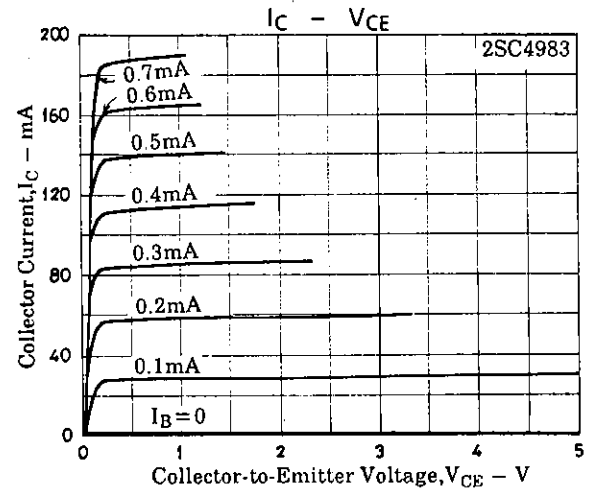
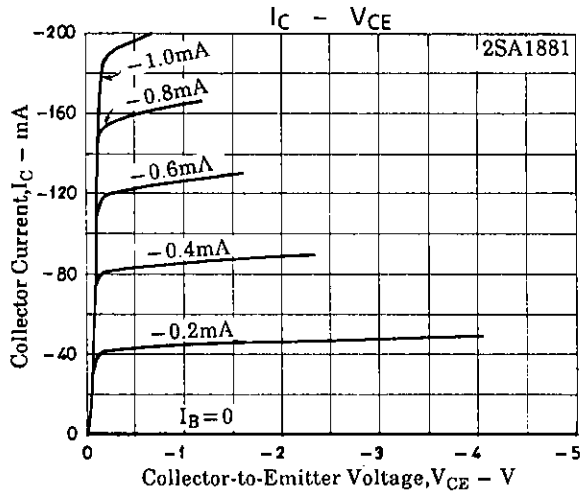
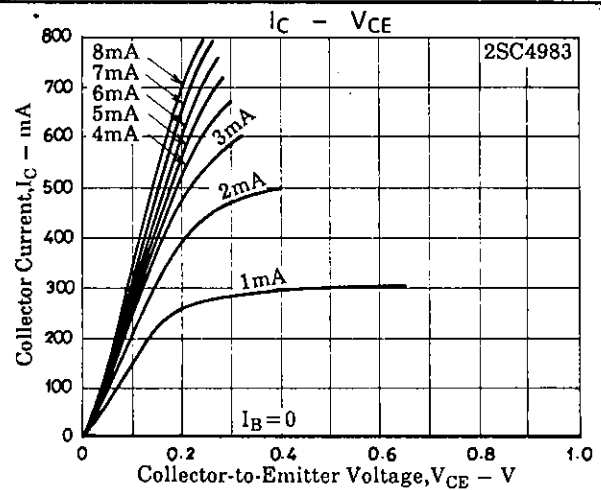
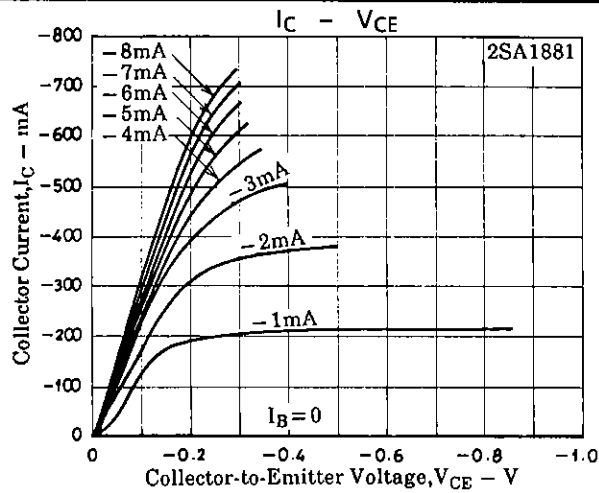
(unit : mm)

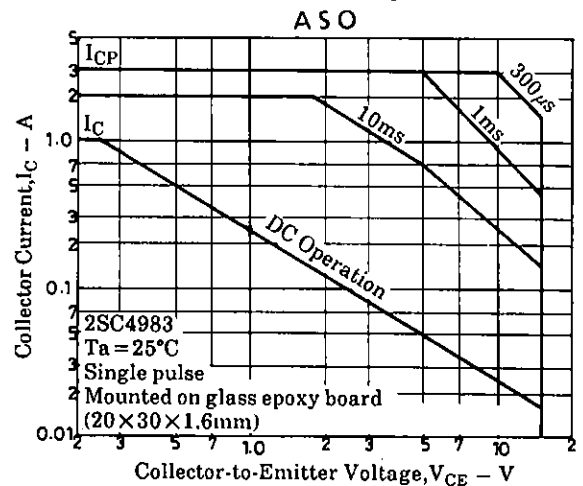
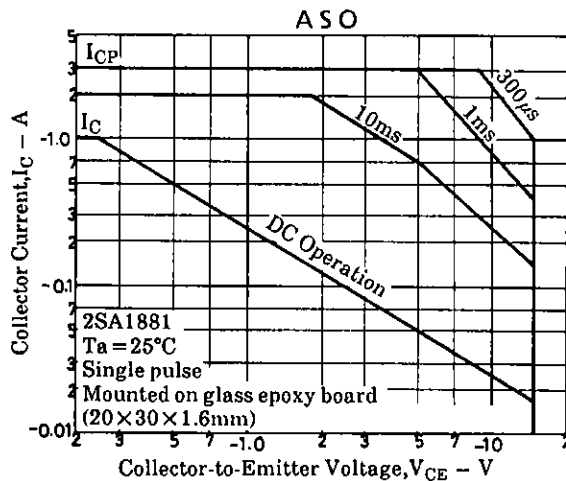
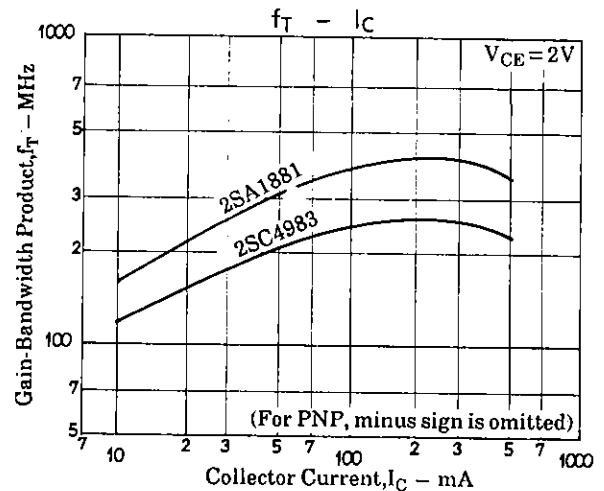
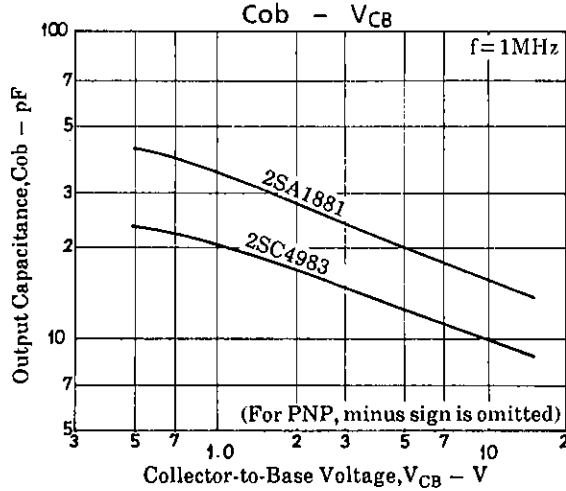
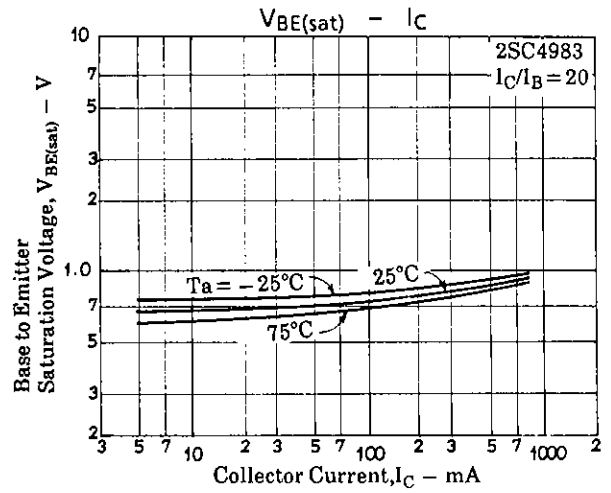
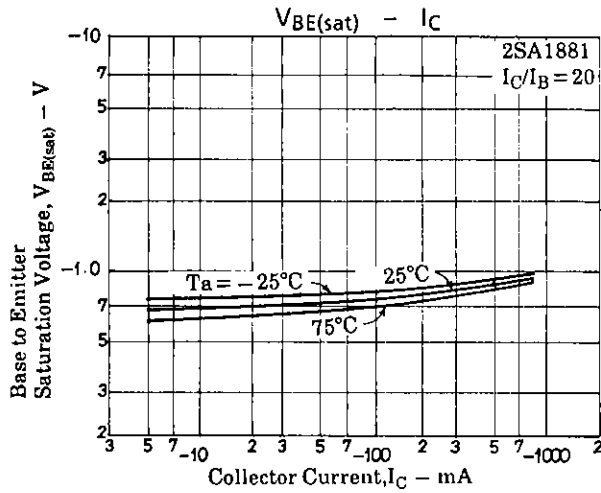
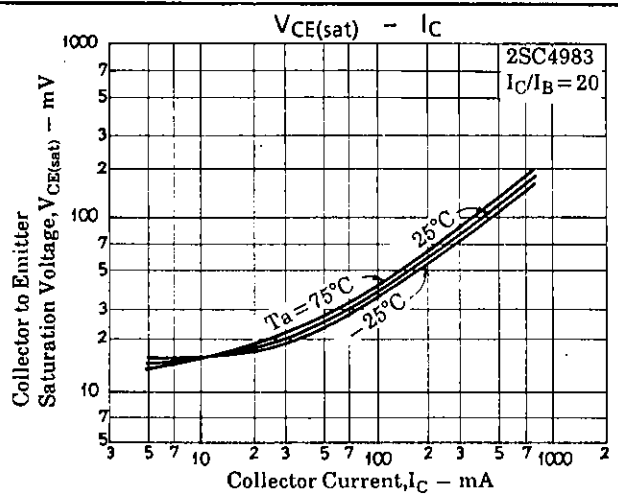
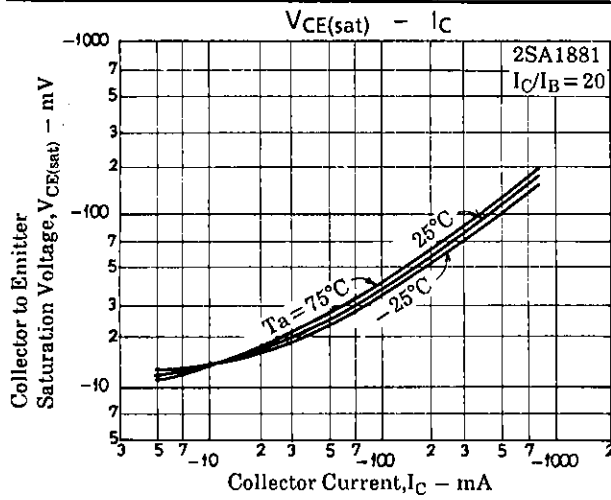


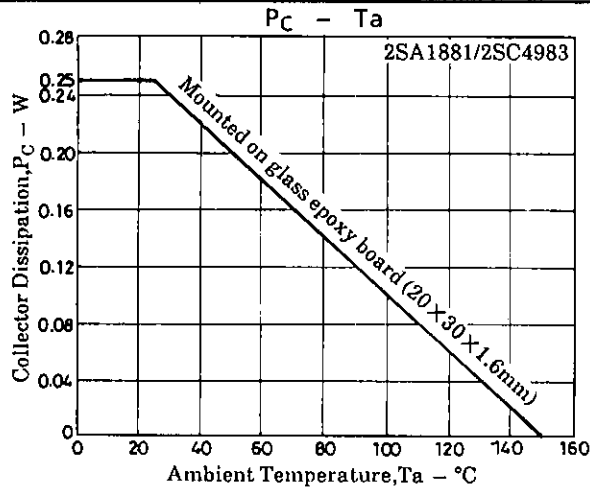
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